

IEEE SF Bay Area MEMS & Sensors Chapter

November 19, 2014

1 http://sites.ieee.org/scv-mems/



Past Meetings

2014	TITLE	Guests	IEEE	Total
Jan. 22 nd	Emerging Trillion Sensors Movement (Dr. Janusz Bryzek)	39	41	80
Feb. 26 th	FBAR and FMOS Technology from a MEMS Perspective	35	35	
	(Dr. Stephen Gilbert)			
	Advanced Metal Eutectic Bonding for High Volume MEMS			
	(Sumant Sood)			70
Mar. 18 th	Coupled-Filed MEMS Simulations (Dr. Metin Ozen)	25	7	32
April 30 th	MEMS Wars: A New Hope (Dr. Kurt Petersen)	37	39	76
May 28 th	MEMS in SEMI – The Role of a Global Association in Advancing	11	12	
	the MEMS Industry (Bettina Weiss)			23
June 25 th	MEMS on Alternate Substrates: A Case Study with Biometric	21	29	
	Sensors (Dr. KG Ganapathi)			50
July 23 rd	AdCom/Volunteers meeting	11	10	21
Aug. 27 th	RF MEMS: From Research to Products (Prof. Gabriel Rebeiz)	30	46	76
Sept. 24 th	IEEE MEMS Happy Hour (No invited talk).	12	12	24
Oct. 22 nd	MEMS-enabled microscopes for in-vivo studies of cancer biology	29	31	60
	Total	250	262	512



Officers and Program Committee

The MEMS and Sensors Chapter is run by volunteers organized as Officers (elected every year), Program Committee, and Advisory Board. If you are interested in volunteering, please send an email to <u>SFBA-MEMS-OFFICERS@listserv.ieee.org</u>.

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Meeting Sponsor

Complimentary food and refreshments sponsored by SoftMEMS Inc.



Tools and Services for Design and Verification of MEMS Products.

Thanks to Dr. Mary Ann Maher, President/CEO





Upcoming Meetings

Feb. 25th, 2015 (Wednesday) 7:45 PM to 8:45 PM. <u>Note: NEW LOCATION!!!</u> *Title*: <u>Building Successful MEMS Company: From Start to IPO</u> *Speaker*: Mr. Steve Nasiri, Nasiri Ventures

Location: Texas Instruments Building E Conference Center, 2900 Semiconductor Dr., Santa Clara, CA 95052 (Directions)

Food: Pizza and beverages will be available at 7:15 pm for a <u>\$5 donation</u> at the door.

Sponsor: Sponsorship opportunities are available. Interested parties please email <u>SFBA-MEMS-OFFICERS@listserv.ieee.org</u>

Mar. 25th, 2015 (Wednesday) 5:30 PM to 7:30 PM. Online registration coming soon. IEEE MEMS and Sensors Happy Hour Location: <u>Steelhead Brewing Company</u>, 333 California Drive, Burlingame, CA 94010

This is a no-host event. Please pay for your own food and drinks.

Sponsor: Sponsorship opportunities are available. Interested parties please email <u>SFBA-MEMS-OFFICERS@listserv.ieee.org</u>



Invited talk by Mr. Holger Doering



Nov. 19th, 2014 (Wednesday) 7:45 PM to 8:45 PM. *Title*: <u>Innovative Pressure Sensing Solutions</u>. *Speaker*: <u>Mr. Holger Doering</u>, COO, Silicon Microstructures, Inc.

Holger Doering is the Chief Operating Officer (COO) at Silicon Microstructures Inc (SMI). He joined SMI in 2007 as a Consultant in Operations, then took over the VP Operations position in 2008 and was promoted to COO in 2011.

He is responsible for Production, Process Engineering, IT, Assembly, Test, and Facilities Management. He started at ELMOS in 1995 as a Process Engineer and became Production Engineering Manager in 1997. From 1999 he was responsible for Production, Process Engineering and Equipment Maintenance in the Plasma-Module of the ELMOS fab. In 2003 he began to transfer the 0.8 µm process from the 6-inch fab in Dortmund to the 8-inch line of the joint ELMOS/ Fraunhofer IMS fab in Duisburg and in 2005 became responsible for the complete 8-inch Operations in Duisburg.

Holger holds a diploma in Electrical Engineering from the University of Dortmund (Germany) with a focus on semiconductor manufacturing. His diploma thesis work was carried out at ELMOS in 1994 where he developed a CMOS-compatible process module to produce monolithic integrated piezoresistive pressure sensors in a EU-funded project.



Innovative Pressure Sensing Solutions

Abstract: Silicon Microstructures Inc (SMI) is a premier semiconductor sensor company developing and manufacturing MEMS-based pressure sensors for automotive, medical, and industrial markets. It has a long history rooted in Silicon Valley since 1991. This talk will present the recent developments in pressure sensor R&D and production at SMI. It will cover the following aspects:

- 1. Company overview on products, R&D and Manufacturing capabilities
- DRIE etch is essential for pressure sensor miniaturization. This talk will present SMI ultra-small pressure sensor development with DRIE process.
- 3. Automated Optical Inspection (AOI) for defect detection in MEMS devices. This talk will cover the application criteria and inspection capabilities.





Innovative Pressure Sensing Solutions

Created by Dr. Shaoxin Lu, Abhishek Davray, Raul Figueroa and Holger Doering

November 18, 2014

Supporting customer success in Automotive, Medical and Industrial markets since 1991

SMI Mission



Enabling our customers' success in improving health, safety, and the environment by providing creative pressure sensing solutions leveraging our leading MEMS technology.













Pioneering Innovation and Expertise



Leader in MEMS-based Pressure Sensing Solutions

- **Lowest pressure**: down to 4 mbar range $(1.5" H_2O)$
- Media Resistant: noble metallization w/ backside entry.
- Smallest size: down to 0.9 mm \times 0.25 mm \times 75 μ m

23 years of development and manufacturing expertise

- 100% subsidiary of Elmos Semiconductor AG (Germany)
- More than **500M sensors sold** into Automotive, Medical, Consumer, HVAC and Industrial markets

Captive Wafer Fab in Silicon Valley (USA)

All functions in one location:

- R&D, Process Development
- Logistics & Quality Control





Company History





Process & Quality - Manufacturing Processes







Product Overview - Areas of Expertise



Low Pressure		Typical Applications: Medical (CPAP), Industrial (HVAC)	Low Pressure Sensor: 4 mbar SMI patented Technologies
Ultra Small	0 cm 1 2	Typical Applications: Automotive (TPMS), Industrial (Barometric)	Ultra-Small Die and Packaged Sensor for OEM Use
Harsh Environment	Class Silcon Glass Class	Typical Applications: Automotive transmission, Diesel Particle Filter (DPF) Exhaust Gas Recirc. (EGR)	Harsh Environment Pressure Sensor Die
Signal-Conditioned		Typical Applications: Respiration Ventilators HVAC & Pressure Transmitters	Dual Chip Intelligent Pressure Sensor, SO-16 Package
Custom Design	.24 mm		Custom Pressure Sensor for Arterial Catheter: (900 x 240 x 75 µm)

Markets and Applications









Medical

Respiration

- CPAP
- Ventilation

Hospital Beds Fluid Evacuation

Blood Pressure

Wound Therapy

Industrial

HVAC

VAV Controllers Pressure Transmitters Liquid Level & Pressure Barometric Pressure Process Control Refrigeration

Automotive

Tire Pressure Monitoring Systems (TPMS) Manifold Air Pressure (MAP) Diesel Particulate Filter (DPF) Exhaust Gas Recirculation (EGR) Oil Pressure Side Air Bag Transmission Oil Pressure Seat Ergonomics

Applications - Medical







Sleep Apnea Treatment

- CPAP (Continuos Positive Airway Pressure)
- Sleep disorder with abnormal pauses in breathing
- CPAP uses mild air pressure to keep an airway open
- -> Feedback of applied air pressure in the mask
- -> µC manages compressor to generate

required pressure

Interventional Cardiology

FFR (Fractional Flow Reserve) guide-wire based procedure
-> accurately measure blood pressure and flow through a specific part of the coronary artery
-> assess whether or not to perform angioplasty and / or stenting on "intermediate" blockages.
-> FFR reduces procedure cost & increases success rate
-> Biocompatibility and blood as harsh environment

Applications - Industrial







Pressure Transmitters/HVAC

- HVAC (Heating, Venting, Air Conditioning)
- Differential pressure transmitters to detect over- / under- and differential pressure.
- -> Monitoring and control of ventilation and air-conditioning, fans and filters.
- -> requires measurement of very
 - low-pressure signals

Valve Positioner

- Intelligent digital valve controllers
- Remote ambient pressure measurement
- -> valve positioning & monitoring of supply pressure
- -> support advances in building technology

and energy efficiency mandates

Applications - Automotive





Tire Pressure Monitoring Systems (TPMS)

- Ultra small absolute pressure sensor for integration in tire inflation valve
- Legislation in USA (2007) requires all new cars to be equipped with TPMS.
- 2013 Europe started with 100% compliance in 2014.
- 2014 South Korea confirmed legislation.
- 2017 Japan intends to legislate.
- 2018 China intends to legislate.
- 2019 India intends to legislate.



Dual-clutch Automated Manual Gearbox

- Backside entry absolute pressure sensor with harsh media compatibility
- Direct contact to hot transmission oil at high pressure in the application

New DSG (Direkt Schalt Getriebe) transmission offers

- better fuel economy
- extremely fast shift times
- no loss of torque during gear shifts
- Pressure sensors monitor correct operation.

Design & Simulation of Advanced Pressure Sensors





Finite Element Modeling

- Optimize structure and predict results
- Mechanical stress and strain
- Resistance and temperature



Process and Device Modeling

- Determine doping profiles from process
- Predict electrical characteristics of devices
- 2D device modeling



Design Rule Checking of Device Layout

- •Verify placement tolerances of electrical components
- Check predicted distances between electrical and mechanical components of MEMS structures

Process Requirements of Advanced Pressure Sensors



 Double side polished wafer processing – defects on wafer backside from conventional handling arms





 Front to Back Alignment and Overlay / IR Measurement





- Stable micro machining technology:
 - Deep Reactive Ion Etching / KOH Etching using Electro Chemical Etch Stop







DRIE – Deep Reactive Ion Etching





Bosch Process

- Silicon etch in SF6 cycle
- Passivation of sidewalls with polymer in C4F8 cycle

DRIE vs KOH Etch

Benefits for DRIE

- Precise control of membrane thickness
- Area reduction for sensors
- Bigger mounting surface, no constraint wafer necessary
- Better accuracy / repeatability

	КОН	DRIE
Membrane Thickness	Controlled by Etch rate / Etch stop	Defined by SOI starting material
Sensor Size	Bigger (with sidewall slope)	Smaller (vertical sidewall)
Mounting Area (% of die)	Smaller (with sidewall slope)	Bigger (vertical sidewall)
Accuracy/Repeatability	Worse (TTV, Etch rate variation)	Better (SOI material control)
Cost	Less expensive	More expensive (factor 3 x variable cost)
Throughput	Batch process (factor 2 x faster than DRIE)	Single wafer process







KOH





Products at SMI that benefit from DRIE



- Ultra small pressure sensors (SM68) for TPMS applications:
 - -> Pressure range from 15 -150 psi
 - -> DRIE formed cavity on backside enabling very small sensor design on SOI
 - -> size reduction of about 60% compared to non DRIE etched sensors
- Ultra Low pressure sensors (SM95) for medical and industrial applications
 - -> Pressure range from 0.15 to 1.5psi
 - -> Backside cavity and pressure range adjustment with DRIE process



SM68 sensor



SM68 sensor DRIE backside cavities



SM95 wafer in front of a lamp showing semitransparent membranes formed by DRIE

 Covered under Patents US 7,111,518 and US 8,381,596 B2

Compensation of DRIE non-uniformities



• CD / Overlay run-out towards the wafer edge

Typical CD distribution in X-direction

- > DRIE CD gets bigger close to wafer edge due to loading effect
- > Cavity shifts in the radial direction at wafer edge due to "outside effect "
- Edge compensation in mask layout to improve CD/Overlay uniformity



Typical cavity overlay distribution in X-direction

DRIE formed cavities for pressure sensors



Buried Cavity Technology --- DRIE reference cavity formed and buried in wafer before sensor /CMOS Foundry process

Comparison	Classic DRIE Approach	Buried Cavity Technology
Process sequence	Sensor foundry -> DRIE	DRIE -> Sensor foundry
Etch time	Long, through wafer etch low throughput	Short, shallow cavity etch high throughput
Cavity CD	Variation across wafer	Precise CD control
Cavity Overlay	Variation across wafer	Minimized Overlay error
Edge excl. Zone	Exclusion zone due to DRIE variance	Nearly no exclusion zone required
CMOS compatibility	Plasma Damage could impact CMOS circuits	Compatible







IR Image

Sensing bridge formed on pre-defined membrane







Automated Optical Inspection (AOI)



- Automated Optical Inspection (AOI) scans the wafer surface and automatically detects defects and classifies them
- ICOS, originating in Belgium and acquired in 2008 by KLA Tencor, built the equipment
- The system is equipped with one central loader and two inspection modules with high speed line cameras







Importance of visual inspection for MEMS devices



 Defects that cannot be caught by electrical tests and cause reliability / performance impacts



Bond Void on the backside -> could cause a leak for absolute pressure sensors



Cracks in Membrane -> falsifies the pressure signal -> reliability problem

Importance of visual inspection for MEMS devices



 Defects that cannot be caught by electrical tests and cause reliability / performance impacts



Mis-shaped cavity

- -> influence on pressure non-linearity
- -> modified sensitivity

Defects in backside metallization

-> could weaken eutectic bond-> reliability problem

Criteria and methods to detect different defects Frontside Inspection





Metal Area

- Inspects for scratches and contamination in the metal region
- Example for the criteria used to detect the defect







Membrane Area

- Inspects for fractures and contamination on the membrane
- Example





Criteria and methods to detect different defects Backside Inspection







Bond Void Area

- Inspects for voids in the bond interface outside the cavity area
- Example





Diaphragm Area

 Inspects for cracks and contamination inside the diaphragm region

570.8

Example

Cavity

Defect Classificati....▽ Area(µm²) Length Width Contrast(GV

36.2

20.7



Inspection at different stages





KOH etched Backside Pre – Metal Inspection



After Metal deposition for Eutectic Bond



DRIE etched Backside before sawing



Backside after sawing -> picture more blurry

Focus on specific defects in the different stages of the process

- Bond interface and membrane defects after bonding
- Defects in backside metal that influence eutectic bond
- Inspection after sawing for saw chipping and cracks

Inspection record to document quality







Sensor Image at Customer Site



SM68 Sensor Image at SMI

- Defect was not on the Die at AOI
- Reassure customer of excellent quality
- -> Defect must have occurred at customer

site, finish with 5D report

Defect Reduction Program



- Screening with AOI after different steps in the process
- Correlation of defect to certain equipment used at that point



Automated defect classification

- type of defect

Wafer ID:6

#Inspected: 25,665

#Pass: 25,051

- area where it is detected
- Shortcut keys for fast Operator reclassification during review

Name

Visual of a wafer map for quick overview for Operators / Engineers

#Reject: 614

#Invalid: 0

front side contamination

saw chip/cracked die other/PCM/missing die

front side scratch

FS litho, metal

Reject Before

Other

Pass

broken diaphragm

30

Slot ID:0

Count

306

214

81

6

4

2

1

25.051

5.315

Yield

97.61%

<u>%</u>

1

1

0

0

0

0 0

98



Color	Name	Output code	Shortcut key
	To be inspected		
	Reject before		
	Pass		F1
	Invalid		
	Reference die		
	Reference die - Invalid		
	Reference die - Not Found	-	
	uneven cavity	62	Num 2
	saw chip/cracked die	63	Num 3
	back side scratch	64	Num 4
	back side contamination	65	Num 5
	broken diaphragm	68	Num 8
	probe reject	66	Num 6
	front side scratch	67	Num 7
	front side contamination	69	Num 9
	discolored field front side	70	1
	etch pit	71	Num *
	front side KOH, stained pad	72	Num -
	deep probe/ no probe marks	73	Num +
	FS litho defect, missing metal	74	Insert
	other/PCM/missing die	75	Home
	delamination/bond void	60	Num 0

Classification and Yield Analysis using Pareto

Classification and Yield Analysis using Pareto





Column1	Column2 💌
front side scratch	1.30%
front side contamination	1.03%
saw chip/cracked die	0.81%
front side KOH/ stained pad	0.27%
other/PCM/missing die	0.21%
delamination/bond void	0.20%
probe reject	0.19%
deep probe/ no probe marks	0.09%
back side contamination	0.01%
broken diaphragm	0.01%
uneven cavity	0.01%
Invalid	0.00%
etch pit	0.00%
discolored field front side	0.00%
back side scratch	0.00%

- Pareto Analysis of Defect types improves the efficiency to increase Yield
- Wafer level Yield has been improved at SMI by 5% as an average over all products in the last 3 years by using Automated Optical Inspection (some products up to 10%)

Automated Classification to reduce time & cost



Comparison	Automated Optical Inspection	100% Operator Inspection
Front and Back Inspection on SM68 Sensor	 25 minutes machine time 0 to 15min. Operator review time per wafer 	~ 8 hours per wafer
Front and Back Inspection on SM95 Sensor	 ~ 10 minutes machine time ~ 5 to 15min. Operator review time per wafer 	~ 2 hours per wafer

- The required throughput of > 40M sensors shipped per year would not have been possible without AOI and not sacrificing quality assurance
- The cost per wafer and the required Operators were reduced significantly
- Customers rely on SMI's quality inspection using AOI as an essential part of the 0ppm automotive strategy

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Thank you !

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